

# BCR25FM-12LB

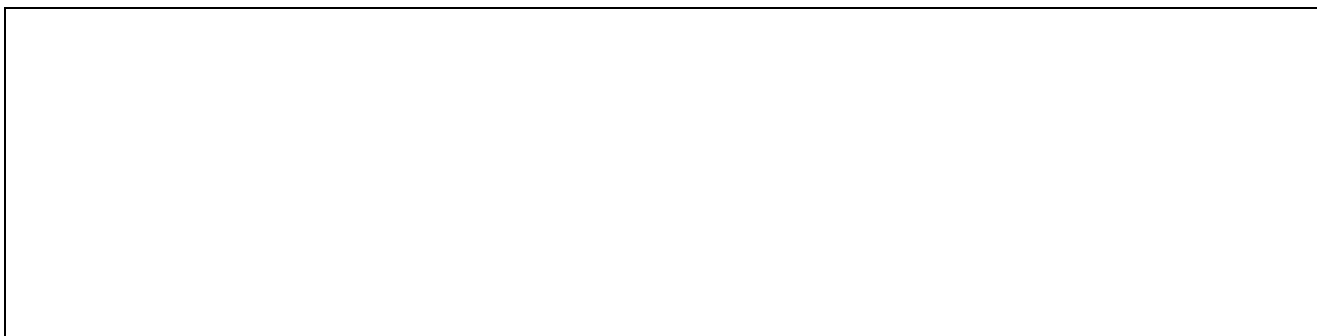
600V - 25A - Triac

Medium Power Use

## Features

- $I_{T(RMS)}$ : 25 A
- $V_{DRM}$ : 600 V
- $T_j$ : 150 °C
- $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 50 mA
- Insulated Type
- Planar Passivation Type
- Viso: 2000 V

## Outline



## Application

Contactless AC switch, electric heater control, Printer, Copier and other general purpose AC control applications.

## Maximum Ratings

Parameter	Symbol	Voltage class	
		12	Unit
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	25	A	Commercial frequency, sine full wave 360° conduction, $T_c = 62\text{ °C}$
Surge on-state current	$I_{TSM}$	250	A	50 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusion	$I^2t$	313	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	

## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I <sub>DRM</sub>	—	—	3.0	mA	T <sub>j</sub> = 125 C, V <sub>DRM</sub> applied
		—	—	5.0	mA	T <sub>j</sub> = 150 C, V <sub>DRM</sub> applied
On-state voltage	V <sub>TM</sub>	—	—	1.5	V	T <sub>c</sub> = 25 C, I <sub>TM</sub> = 40A, instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	V <sub>FGT</sub>	—	—	2.0	V	T <sub>j</sub> = 25 C, V <sub>D</sub> = 6 V, R <sub>L</sub> = 6 Ω, R <sub>G</sub> = 330 Ω
	V <sub>RGT</sub>	—	—	2.0	V	
	V <sub>RGT</sub>	—	—	2.0	V	
Gate trigger current <sup>Note2</sup>	I <sub>FGT</sub>	—	—	50	mA	T <sub>j</sub> = 25 C, V <sub>D</sub> = 6 V, R <sub>L</sub> = 6 Ω, R <sub>G</sub> = 330 Ω
	I <sub>RGT</sub>	—	—	50	mA	
	I <sub>RGT</sub>	—	—	50	mA	
Gate non-trigger voltage	V <sub>GD</sub>	0.2	—	—	V	T <sub>j</sub> = 125 C, V <sub>D</sub> = 1/2 V <sub>DRM</sub>
		0.1	—	—		T <sub>j</sub> = 150 C, V <sub>D</sub> = 1/2 V <sub>DRM</sub>
Thermal resistance	R <sub>th(j-c)</sub>	—	—	2.8	C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note4</sup>	(dv/dt) <sub>c</sub>	10	—	—	V/ s	T <sub>j</sub> = 125 C
		1	—	—		T <sub>j</sub> = 150 C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance R<sub>th(c-f)</sub> in case of greasing is 0.5 C/W.

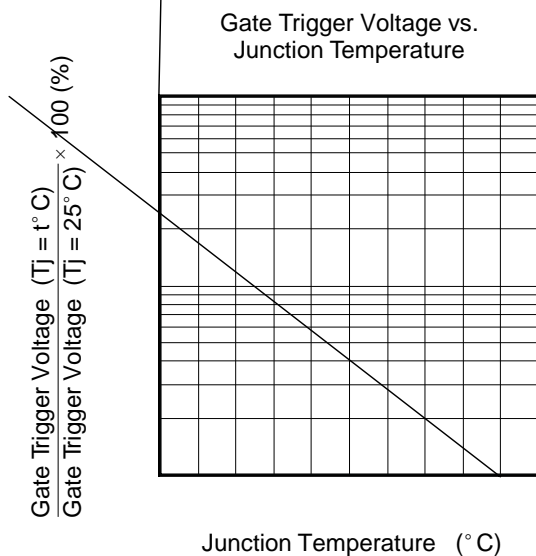
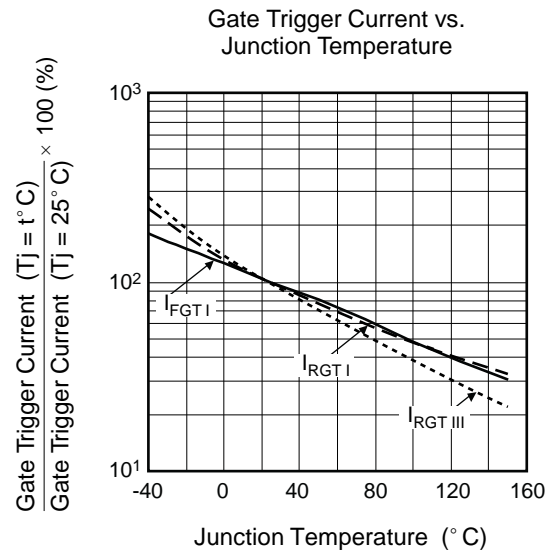
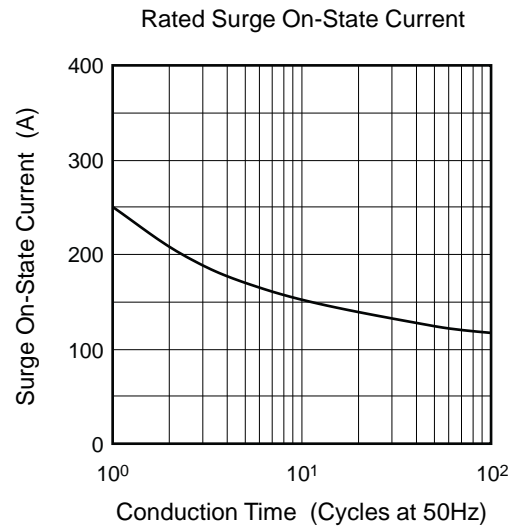
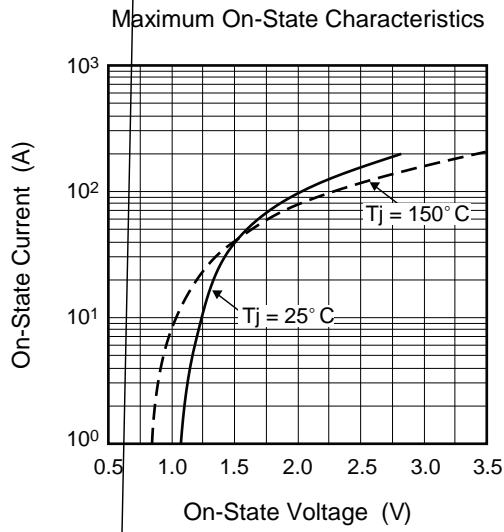
4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

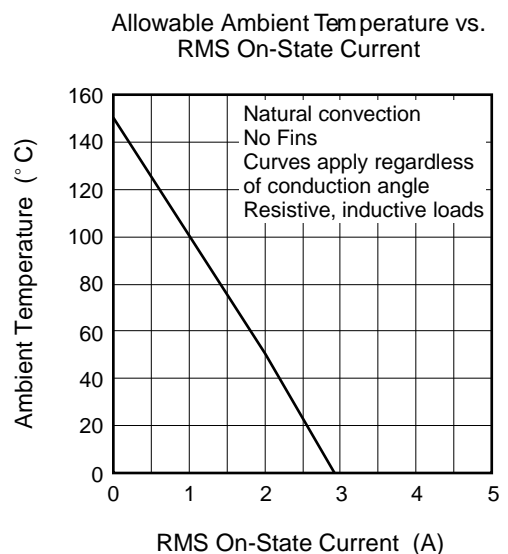
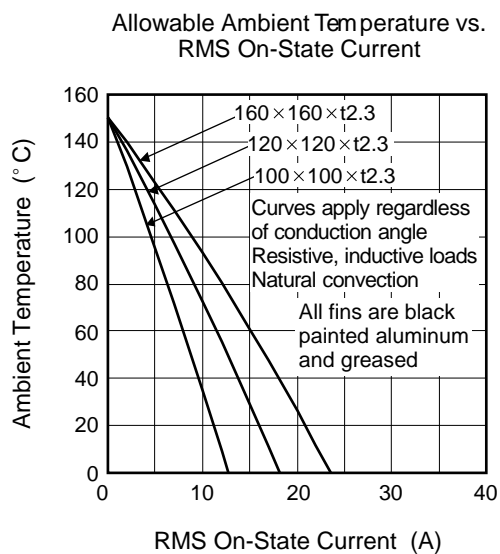
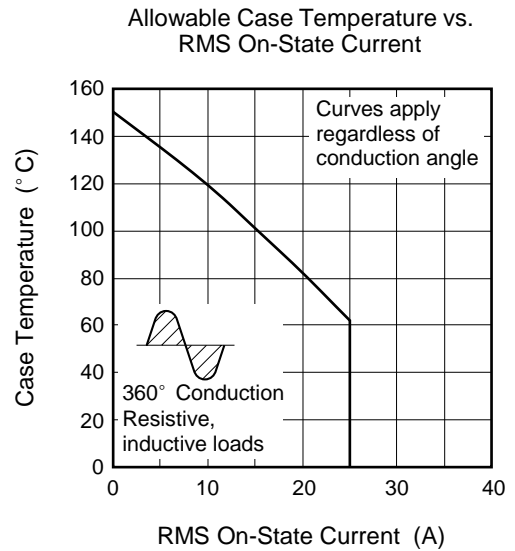
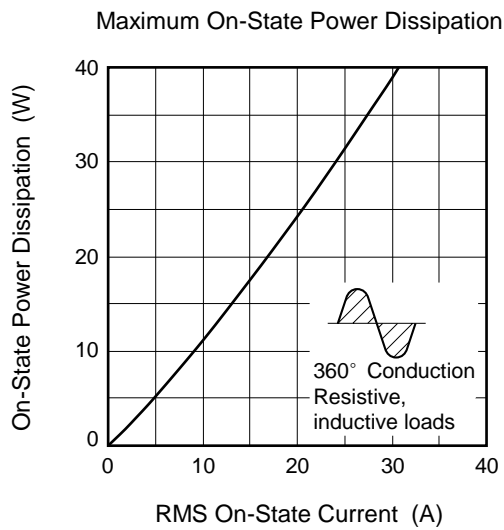
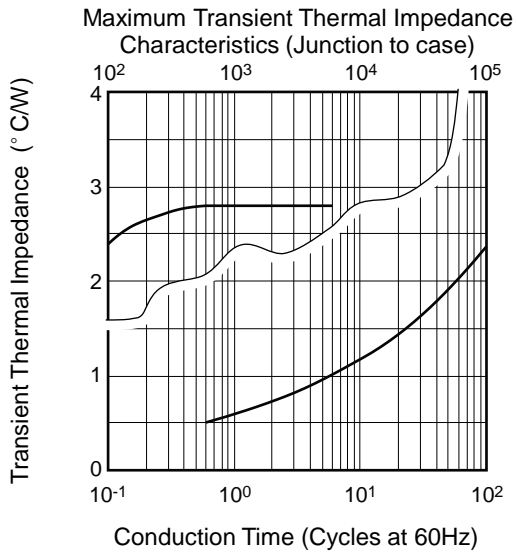
5. Make sure that your finished product containing this device meets your safe isolation requirements.

For safety, it's advisable that heatsink is electrically floating.

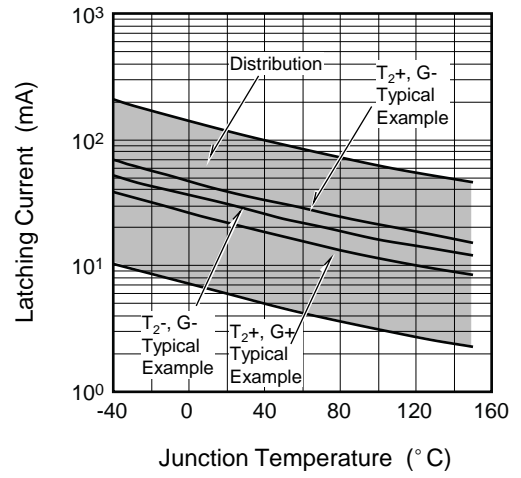
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature T <sub>j</sub> = 125 °C / 150 °C 2. Rate of decay of on-state commutating current (di/dt) <sub>c</sub> = - 13 A/ms 3. Peak off-state voltage V <sub>D</sub> = 400 V	

Performance Curves

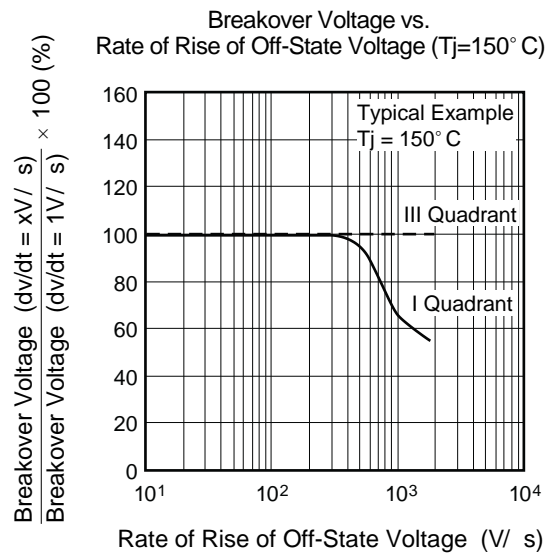
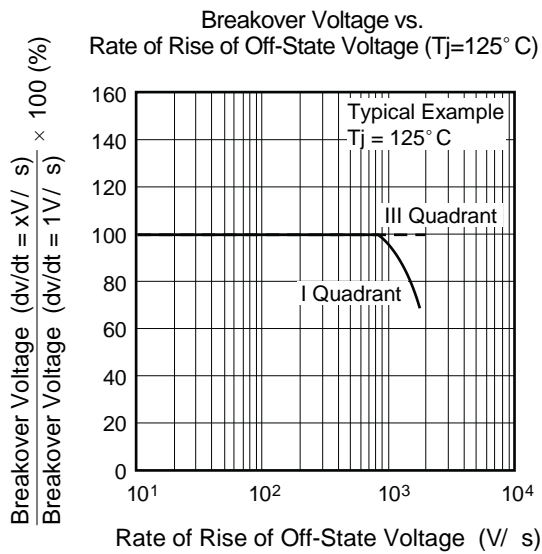




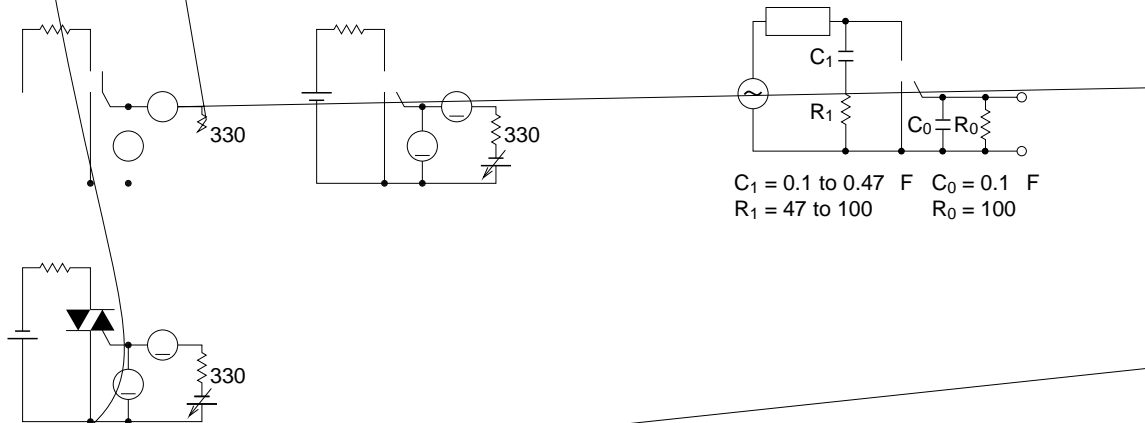
Latching Current vs. Junction Temperature



Junction T



Gate Trigger Characteristics Test Circuits

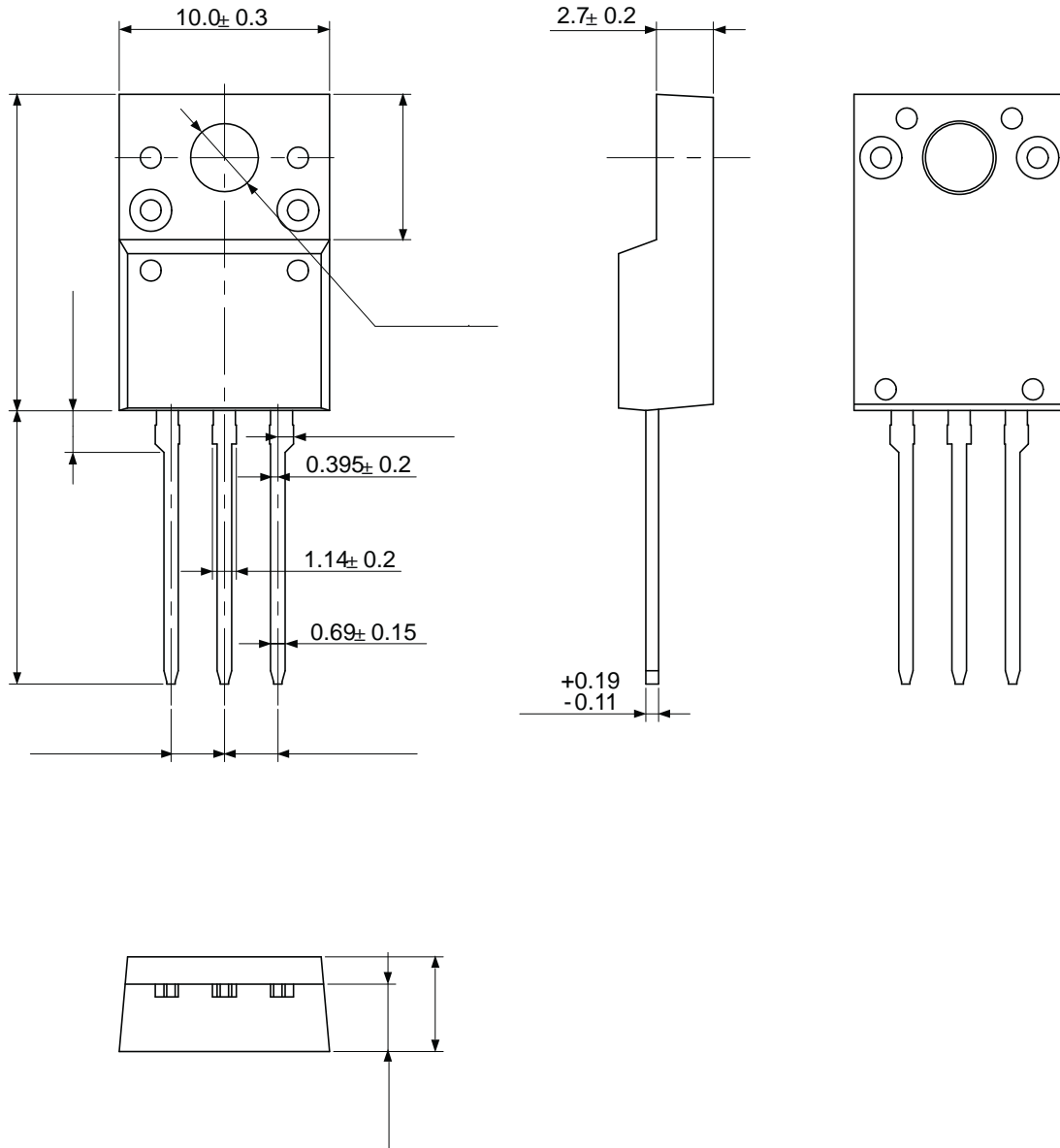


### Package Dimensions

Ordering code: #BH0

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
-	PRSS0003AP-A	TO-220FPA	1.65

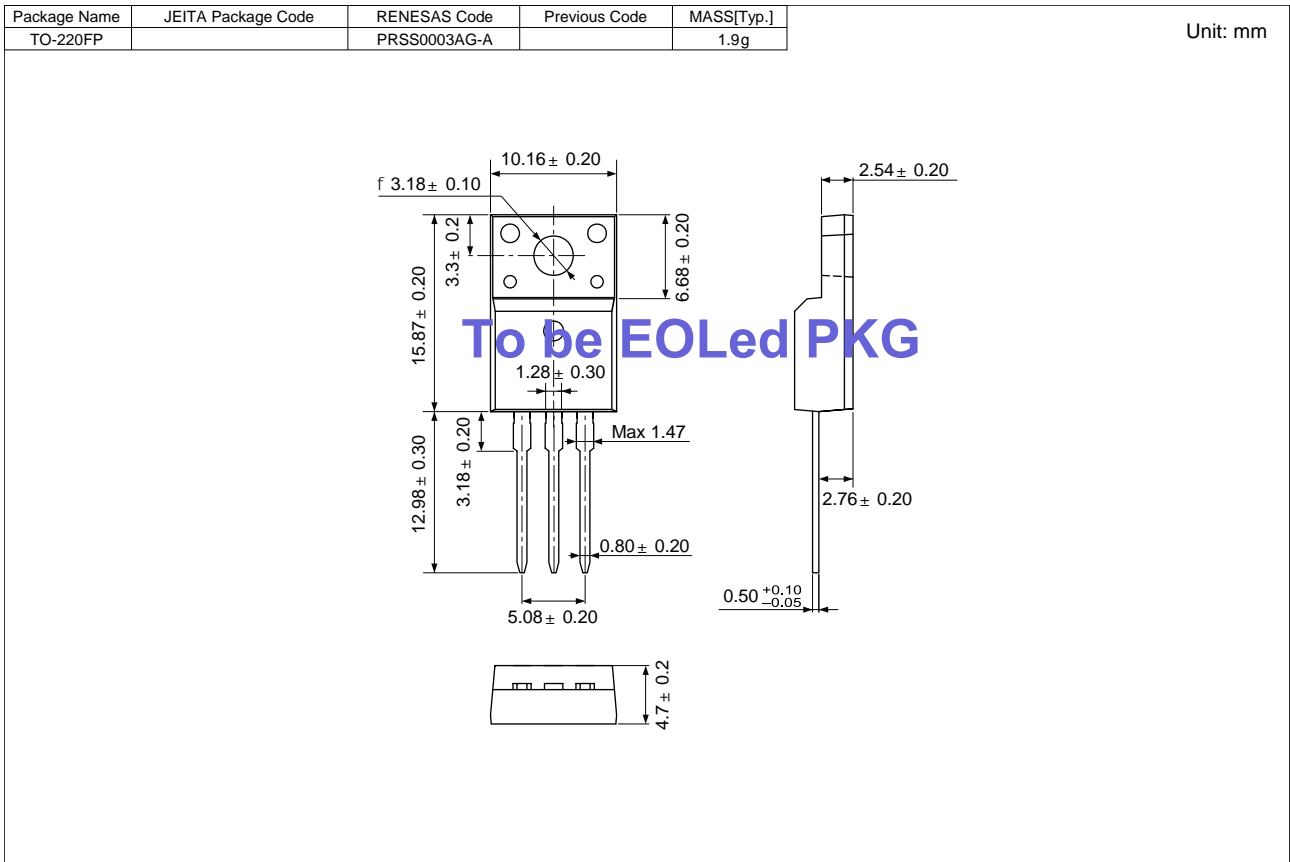
Unit: mm



1

### Package Dimensions

Ordering code: #BB0 <To be EOLed>



### Ordering Information

Orderable Part Number	Package	Quantity <sup>Note6</sup>	Remark	Status
BCR25FM-12LB#BH0	TO-220FPA	50 pcs./ tube	Straight type	Under Development
BCR25FM-12LB□□#BH0	TO-220FPA	50 pcs./ tube	□□:Lead form type	
BCR25FM-12LB#BB0	TO-220FP	50 pcs./ tube	Straight type	EOL Candidate

Notes: 6. Please confirm the specification about the shipping in detail.



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